IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

B. Amendments to the Specification.

Please substitute the paragraph starting at Page 4, Line 12 with the following:

In this way, a memory cell may include complementary data nodes. Such an arrangement may be particularly applicable to higher speed memory devices, such as static random access memories (SRAMs), dual port RAMs, and content address memories (CAMs), to name just a few.

10